AMENDMENTS TO THE CLAIMS

Please amend Claim 7, 9, and 10 to read as follows:

G1

7. (Currently Amended) A semiconductor device comprising a ~~substrate and formed thereon an~~ single-crystal silicon active layer used for photoelectric conversion and having a ~~the surface~~ (111)-plane~~, the active layer being used in photoelectric conversion, where~~ as its surface, wherein an angle formed by any arbitrary two cutting lines contained in the surface and not coming into coincidence is represented by θ, and θ satisfies the expression ~~the active layer has a cutting angle of~~ $|\cos\theta| = 1/2$ or $3^{1/2}/2$.

G2

9. (Currently Amended) The semiconductor device according to Claim 7, wherein ~~the~~ any deviation of said surface from said ~~the strict~~ (111) plane is within an angle equal to 24/60ths of a degree (0°24').

10. (Currently Amended) A photoelectric conversion element comprising an anti-reflection layer, ~~semiconductor~~ silicon layers, and an electrode, provided from ~~the~~ a light incident side,

wherein all of the silicon layers are ~~epitaxial~~ single-crystal silicon layers, and wherein the silicon layers comprise an n^+ layer, and a p^- layer of about 30 μm thickness, provided from the light incident side, wherein a surface of the silicon layers has a (111) plane, and wherein any deviation of said surface from said (111) plane is within an angle equal to 24/60ths of a degree (0°24') .